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### **UPS540e3**

### 5 A Schottky Barrier Rectifier

#### DESCRIPTION

This UPS540e3 in the Powermite3® package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3® package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

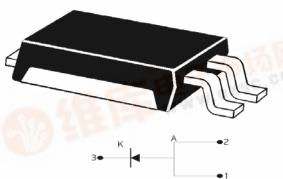
DOOL LITE MANYIMALIMA DATIMOO

(UNLESS OTHERWISE SPECIFIED)			
Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	40	V
RMS Reverse Voltage	V <sub>R (RMS)</sub>	28	V
Average Rectified Output Current	Io	5	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load@ T <sub>c</sub> =90 °C	I <sub>FSM</sub>	100	A
Storage Temperature	$T_{STG}$	-55 to +150	°C
Junction Temperature	TJ	-55 to +125	°C

THERMAL CHARACTERISTICS			
Thermal Resistance			_
Junction-to-case (bottom)	R <sub>eJC</sub>	3.2	°C/ Watt
Junction to ambient (1)	$R_{\theta JA}$	65	°C/ Watt

(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print

#### Powermite 3™



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#### **KEY FEATURES**

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm
- Options for screening in accordance with MIL-PRF-19500 for JAN, JANTX, and JANTXV are available by adding MQ, MX, or MV prefixes respectively to part numbers. For example, designate MXUPS540e3 for a JANTX (consult factory for Tin-Lead plating).
- Optional 100% avionics screening available by adding MA prefix for 100% temperature cycle, thermal impedance and 24 hours HTRB (consult factory for Tin-Lead plating)

#### **APPLICATIONS/BENEFITS**

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I<sub>RM</sub>
- Small foot print
   190 X 270 mils (1:1 Actual size)
   See mounting pad details on pg 3

#### **MECHANICAL & PACKAGING**

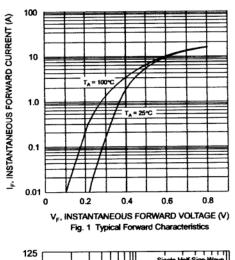
- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S540•
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel



## **5 A Schottky Barrier Rectifier**

Donomoton	Cymahal	Conditions	N/II:	T	Max	l lm:4a
Parameter	Symbol	Conditions	Min	Тур.	Max	Units
Forward Voltage (Note 1)		I <sub>F</sub> = 5 A , T <sub>j</sub> = 25 °C		0.47	0.54	
	V <sub>F</sub>	$I_F = 5 \text{ A}$ , $T_j = 125 ^{\circ}\text{C}$		0.45		V
	V F	$I_F = 10 \text{ A}$ , $T_j = 25 ^{\circ}\text{C}$		0.62		•
		I <sub>F</sub> = 10 A , T <sub>j</sub> = 125 °C		0.59		
Reverse Break Down Voltage Note 1)	$V_{BR}$	I <sub>R</sub> = 0.5 mA	40			V
Reverse Current (Note1)		$V_R = 40 \text{ V}, T_i = 25^{\circ}\text{C}$		0.030	0.5	
	I <sub>F</sub>	$V_R = 40 \text{ V}, T_j = 125 ^{\circ}\text{C}$		2.5	20	mA
Capacitance	Ст	$V_R = 4 \text{ V}; F = 1 \text{ MH}_Z$		250		pF

Note: 1 Short duration test pulse used to minimize self – heating effect



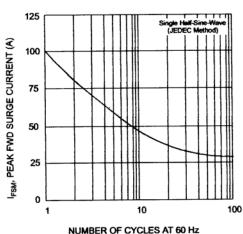
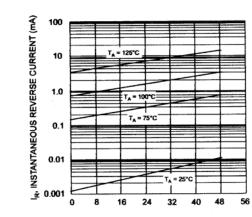


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current



V<sub>R</sub>, INSTANTANEOUS, REVERSE VOLTAGE (V) Fig. 2 Typical Reverse Characteristics

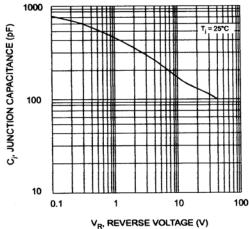
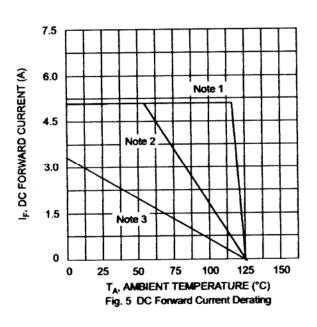
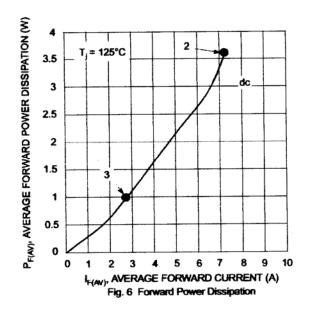


Fig. 4 Typical Junction Capacitance

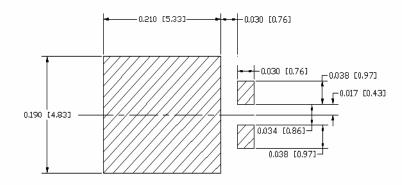


## 5 A Schottky Barrier Rectifier





- Notes: 1.  $T_A = T_{SOLDERING\ POINT}$ ,  $R_{\Theta JS} = 3.2^{\circ}$ C/W,  $R_{\Theta sa} = 0^{\circ}$  C/W. 2. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0".  $R_{\Theta JA}$  in range of 15-30° C/W.
  - 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout  $R_{\Theta JA}$  in range of 65° C/W. See mounting pad below.

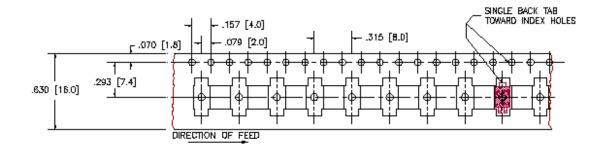


Mounting Pad Dimensions: inches [mm]

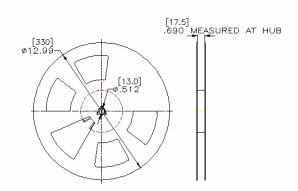


## **5 A Schottky Barrier Rectifier**

#### 16 mm TAPE



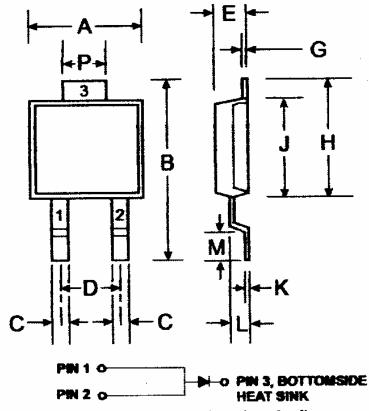
### 13 INCH REEL





## **5 A Schottky Barrier Rectifier**

#### **DIMENSIONS**



		HEAT WHAT
Note:	Pins 1 &	2 must be electrically
	connecte	ed at the printed circuit board

POWERMITE®3			
Dim	Min	Max	
A	4.03	4.09	
В	6.40	6.61	
С	.889 NOM		
D	1.83 NOM		
E	1.10	1.14	
G	.178 NOM		
н	5.01	5.17	
J	4.37	4.43	
K	.178 NOM		
L	.71	.77	
M	.36	.46	
P	1.73	1.83	
All Dimensions in mm			

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NOTES: